

M5M5256DFP, VP, RV-10VLL, -12VLL, -15VLL, -10VXL, -12VXL, -15VXL

262144-BIT (32768-WORD BY 8-BIT) CMOS STATIC RAM

DESCRIPTION

This M5M5256DFP, VP, RV is a 262144-bit CMOS static RAMs organized as 32768-words by 8-bits which is fabricated using high-performance 3 polysilicon CMOS technology. The use of resistive load NMOS cells and CMOS periphery result in a high-density and low-power static RAM. They are low stand-by current and low voltage operation (3V) and ideal for the battery operation application.

Especially the M5M5256DVP, RV are packaged in a 28-pin thin small outline package. Two types of devices are available, M5M5256DVP (normal lead bend type package) and M5M5256DRV (reverse lead bend type package). Using both type of devices, it becomes very easy to design a printed circuit board.

FEATURES

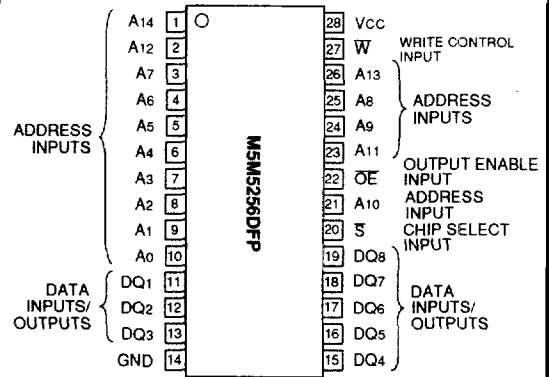
Type name	Access time (max)	Power supply current	
		Active (max)	stand-by (max)
M5M5256DFP, VP, RV-10VLL	100ns	20mA (V _{CC} =3.6V)	12μA
M5M5256DFP, VP, RV-12VLL	120ns		(V _{CC} =3.6V)
M5M5256DFP, VP, RV-15VLL	150ns		
M5M5256DFP, VP, RV-10VXL	100ns		2.4μA (V _{CC} =3.6V)
M5M5256DFP, VP, RV-12VXL	120ns		0.05μA (V _{CC} =3V, Typical)
M5M5256DFP, VP, RV-15VXL	150ns		

- Single +2.7V~3.6V power supply
- No clocks, No refresh
- Data-hold on +2V power supply
- Directly TTL compatible: All inputs and outputs
- Three-state outputs: OR-tie capability
- Simple memory expansion by \bar{S}
- \bar{OE} prevents data contention in the I/O bus
- Common data I/O
- Low stand-by current 0.05μA (typ)
- Package
 - M5M5256DFP 28pin 450mil SOP
 - M5M5256DVP, RV 28pin 8 X 13.4mm² TSOP

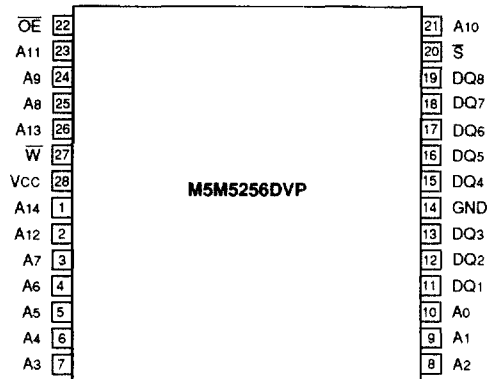
APPLICATION

Small capacity memory units

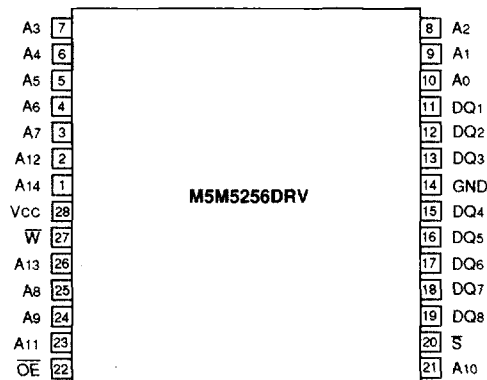
PIN CONFIGURATION (TOP VIEW)



Outline 28P2W-C



Outline 28P2C-A



Outline 28P2C-B

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FUNCTION

The operation mode of the M5M5256DFP, VP, RV is determined by a combination of the device control inputs \bar{S} , \bar{W} and \bar{OE} . Each mode is summarized in the function table.

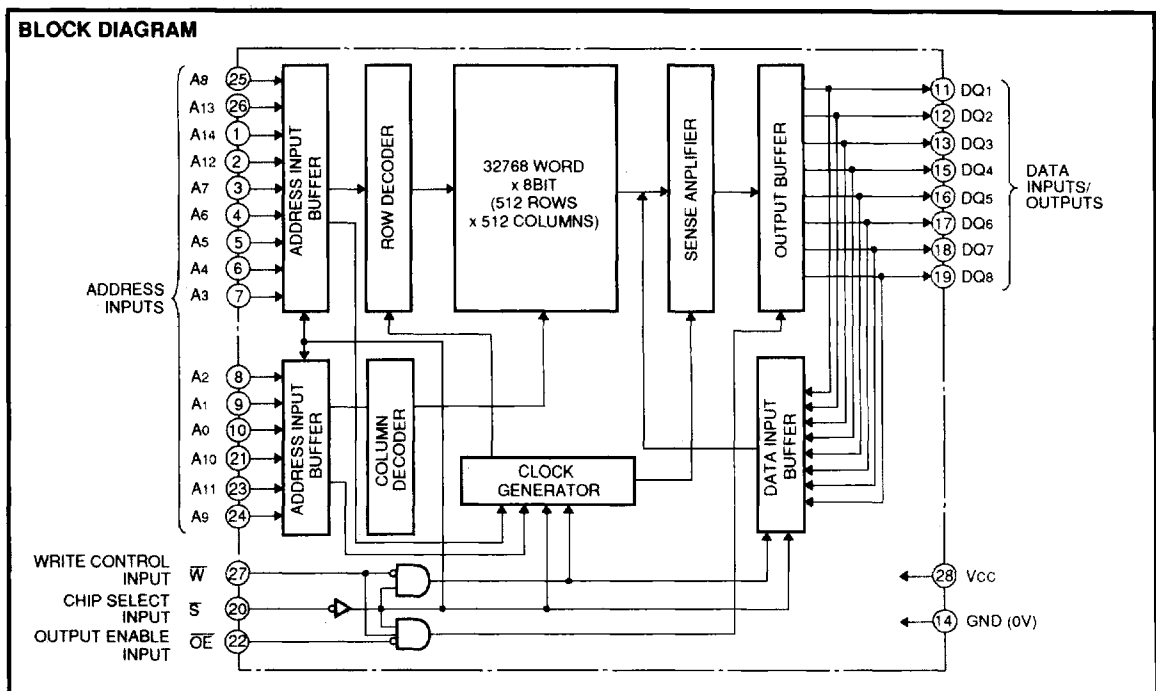
A write cycle is executed whenever the low level \bar{W} overlaps with the low level \bar{S} . The address must be set up before the write cycle and must be stable during the entire cycle. The data is latched into a cell on the trailing edge of \bar{W} , \bar{S} , whichever occurs first, requiring the set-up and hold time relative to these edge to be maintained. The output enable \bar{OE} directly controls the output stage. Setting the \bar{OE} at a high level, the output stage is in a high-impedance state, and the data bus contention problem in the write cycle is eliminated.

A read cycle is executed by setting \bar{W} at a high level and \bar{OE} at a low level while \bar{S} are in an active state.

When setting \bar{S} at a high level, the chip is in a non-selectable mode in which both reading and writing are disabled. In this mode, the output stage is in a high-impedance state, allowing OR-tie with other chips and memory expansion by \bar{S} . The power supply current is reduced as low as the stand-by current which is specified as I_{CC3} or I_{CC4} , and the memory data can be held +2V power supply, enabling battery back-up operation during power failure or power-down operation in the non-selected mode.

FUNCTION TABLE

\bar{S}	\bar{W}	\bar{OE}	Mode	DQ	I _{CC}
H	X	X	Non selection	High-impedance	Stand-by
L	L	X	Write	D _{IN}	Active
L	H	L	Read	D _{OUT}	Active
L	H	H		High-impedance	Active



MITSUBISHI LSIs

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ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings	Unit
V _{CC}	Supply voltage		-0.3~4.6	V
V _I	Input voltage	With respect to GND	-0.3*~V _{CC} +0.3 (max. 4.6)	V
V _O	Output voltage		0~V _{CC}	V
P _d	Power dissipation	T _a =25°C	700	mW
T _{opr}	Operating temperature		0~70	°C
T _{stg}	Storage temperature		-65~150	°C

* -3.0V in case of AC (Pulse width ≤ 30ns)

DC ELECTRICAL CHARACTERISTICS (T_a=0~70°C, V_{CC}=2.7~3.6V, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V _{IH}	High-level input voltage		2.0		V _{CC} +0.3	V
V _{IL}	Low-level input voltage		-0.3*		0.6	V
V _{OH}	High-level output voltage	I _{OH} =-0.5mA I _{OH} =-0.05mA	2.4		V _{CC} -0.5	V
V _{OL}	Low-level output voltage	I _{OL} =1mA			0.4	V
I _I	Input leakage current	V _I =0~V _{CC}			±1	μA
I _O	Output leakage current	\bar{S} =V _{IH} or \bar{OE} =V _{IH} , V _{IO} =0~V _{CC}			±1	μA
I _{CC1}	Active supply current (AC, MOS level)	\bar{S} ≤ 0.2V Other inputs ≤ 0.2V or ≥ V _{CC} -0.2V Output open	Min. cycle	11	20	mA
			1MHz	1.5	3	
I _{CC2}	Active supply current (AC, TTL level)	\bar{S} =V _{IL} Other inputs=V _{IH} or V _{IL} Output open	Min. cycle	11	20	mA
			1MHz	1.5	3	
I _{CC3}	Stand-by supply current	\bar{S} ≥ V _{CC} -0.2V Other inputs=0~V _{CC}	-VLL		12	μA
			-VXL	0.05	2.4	
I _{CC4}	Stand-by supply current	\bar{S} =V _{IH} , Other inputs=0~V _{CC}			0.33	mA
C _I	Input capacitance (T _a =25°C)	V _I =GND, V _I =25mVrms, f=1MHz			6	pF
C _O	Output capacitance (T _a =25°C)	V _O =GND, V _O =25mVrms, f=1MHz			8	pF

* -3.0V in case of AC (Pulse width ≤ 30ns)

Note1: Direction for current flowing into IC is indicated as positive. (no mark)

2: Typical value is 3V, T_a=25°C.

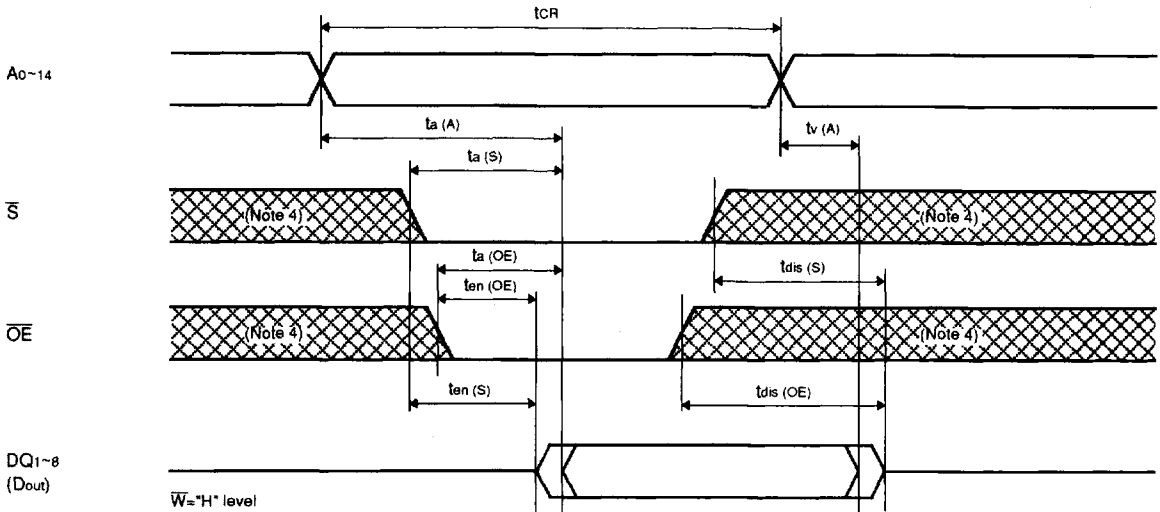
3: C_I, C_O are periodically sampled and are not 100% tested.

**M5M5256DFP,VP,RV-10VLL,-12VLL,-15VLL,
-10VXL,-12VXL,-15VXL**

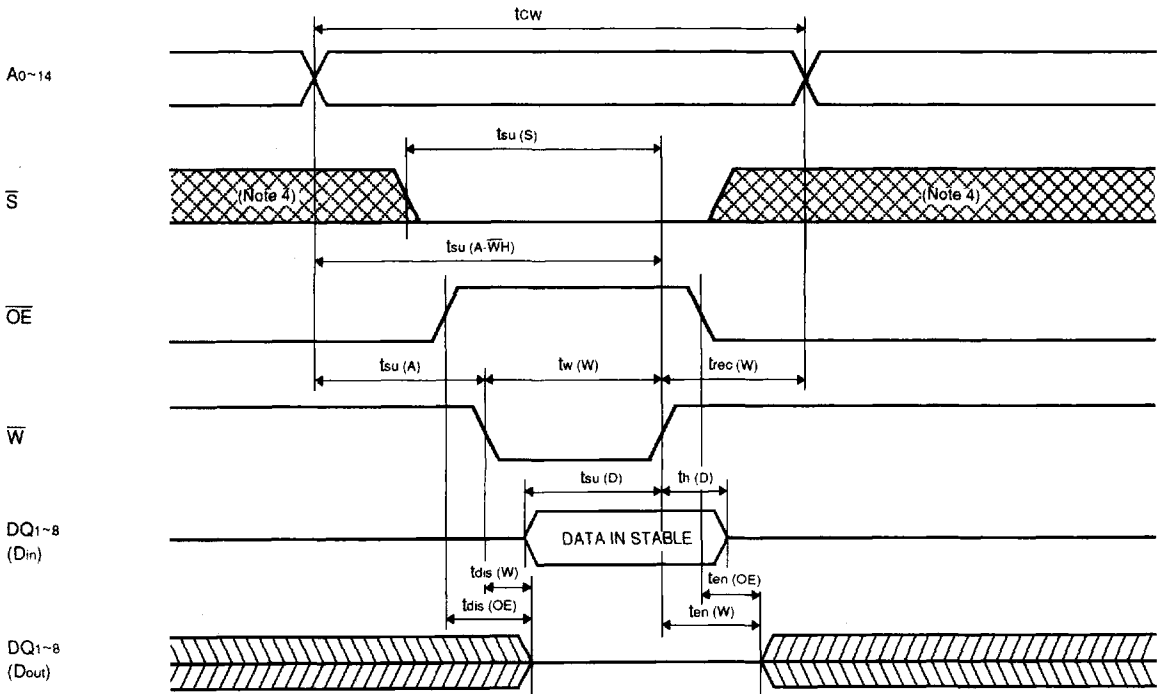
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(4) TIMING DIAGRAMS

Read cycle



Write cycle (\bar{W} control mode)

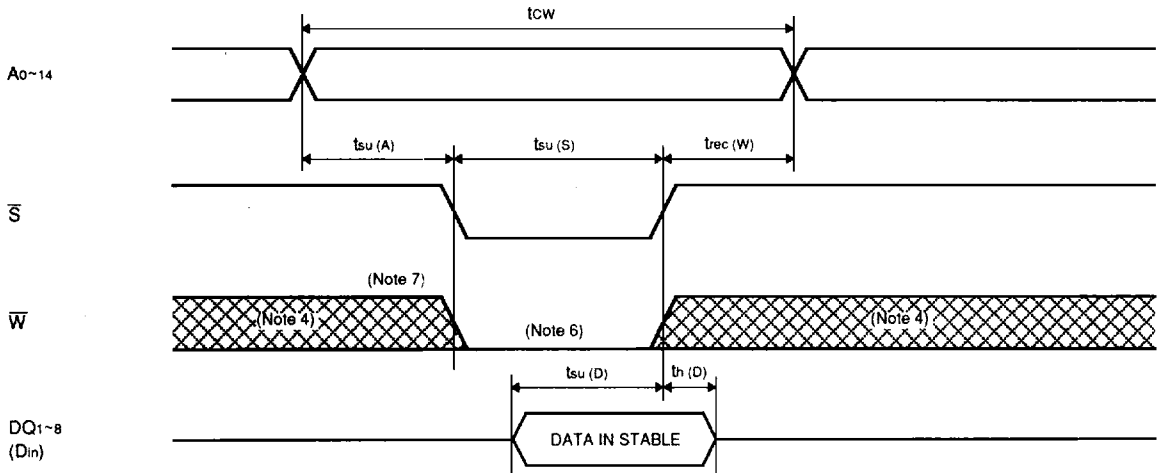


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Write cycle (\overline{S} control mode)



- Note 4: Hatching indicates the state is don't care.
 Note 5: Writing is executed in overlap of \overline{S} and \overline{W} low.
 Note 6: If \overline{W} goes low simultaneously with or prior to \overline{S} , the output remains in the high-impedance state.
 Note 7: Don't apply inverted phase signal externally when DQ pin is in output mode.
 Note 8: t_{en} , t_{dis} are periodically sampled and are not 100% tested.

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POWER DOWN CHARACTERISTICS

(1) ELECTRICAL CHARACTERISTICS (Ta=0~70°C, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V _{CC} (PD)	Power down supply voltage		2			V
V _I (\bar{S})	Chip select input \bar{S}		2			V
I _{CC} (PD)	Power down supply current	V _{CC} =3V Other inputs=3V	-VLL		10*	μA
			-VXL	0.05	2**	μA

* Ta=25°C, I_{CC} (PD)=1μA

** Ta=25°C, I_{CC} (PD)=0.2μA

(2) TIMING REQUIREMENTS (Ta=0~70°C, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
t _{su} (PD)	Power down set up time		0			ns
t _{rec} (PD)	Power down recovery time		t _{CR}			ns

(3) POWER DOWN CHARACTERISTICS

